High Power Bipolar Transistor





Features:

- Collector-Emitter sustaining voltage V_{CEO(sus)} = 60V (Min.) TIP31A, TIP32A
 = 100V (Min.) TIP31C, TIP32C
- Collector-Emitter saturation voltage $V_{CE(sat)} = 1.2V \text{ (Max.)}$ at $I_C = 3A$
- Current gain-bandwidth product $f_T = 3MHz$ (Min.) at $I_C = 500mA$

Maximum Ratings

Characteristic	Symbol	TIP31A TIP32A	TIP31C TIP32C	Unit
Collector-Emitter Voltage	V _{CEO}	60	100	V
Collector-Base Voltage	V _{CBO}	60		
Emitter-Base Voltage	V _{EBO}	5		
Collector Current-Continuous -Peak	I _C	3 5		А
Base Current	I _B	1		
Total Power Dissipation at T _C = 25°C Derate above 25°C	P _D	40 0.32		W W/°C
Operation and Storage Junction Temperature Range	T _J , T _{STG}	-65 to	+150	°C

Thermal Characteristics

Characteristic	Symbol	Max.	Unit
Thermal Resistance Junction to Case	$R_{ heta jc}$	3.125	°C/W



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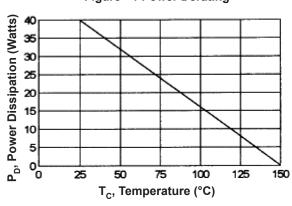


Electrical Characteristics (T_C = 25°C unless otherwise noted)

Chara	acteristic	Symbol	Min.	Max.	Unit	
OFF Characteristics		•			•	
Collector-Emitter Sustaining Vol $I_C = 30$ mA, $I_B = 0$	oltage (1) TIP31A, TIP32A TIP31C, TIP32C	V _{CEO(sus)}	60 100	-	V	
Collector Cut off Current $V_{CE} = 30V$, $I_{B} = 0$ $V_{CE} = 60V$, $I_{B} = 0$	TIP31A, TIP32A TIP31C, TIP32C	I _{CEO}	-	0.3		
Collector Cut off Current $V_{CE} = 60V, V_{EB} = 0$ $V_{CE} = 100V, V_{EB} = 0$	TIP31A, TIP32A TIP31C, TIP32C	I _{CES}	-	0.2	mA	
Emitter Cut off Current $V_{EB} = 5V$, $I_{C} = 0$		I _{EBO}	-	1		
ON Characteristics (1)						
DC Current Gain $I_C = 1A$, $V_{CE} = 4V$ $I_C = 3A$, $V_{CE} = 4V$		h _{FE}	25 10	- 50	-	
Collector-Emitter Saturation Vo $I_C = 3A, I_B = 375mA$	oltage	V _{CE(sat)}	-	1.2		
Base-Emitter On Voltage $I_C = 3A, V_{CE} = 4V$		$V_{BE(on)}$	-	1.8	V	
Dynamic Characteristics			· · · · ·			
Current Gain-Bandwidth Produ $I_C = 500$ mA, $V_{CE} = 10$ V, $f_{TEST} = 10$	` '	f _T	3	-	MHz	
Small Signal Current Gain I _C = 500mA, V _{CE} = 10V, f = 1kH		h _{FE}	20	-	-	

⁽¹⁾ Pulse Test: Pulse width ≤300µs, Duty Cycle ≤2%





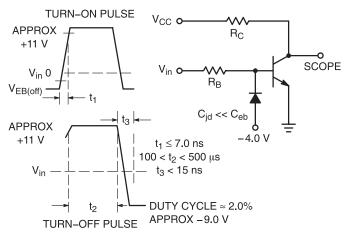


⁽²⁾ $f_T = h_{FE} \cdot f_{TEST}$

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Figure - 2 Switching Time Equivalent Circuit



 $R_{\rm B}$ and $R_{\rm C}$ Varied to Obtain Desired Current Levels

Figure - 3 Turn-On Time $I_{\rm C}/I_{\rm B}=10$ $T_J = 25^{\circ}C$ $t_r @ V_{CC} = 30 V$ $t_r @ V_{CC} = 10 V$ $t_d @ V_{EB(off)} = 2.0 V$

2.0

1.0

0.7

0.5

0.3

0.1

0.07

0.05

0.03

0.03

0.05

0.1

t, Time (µs)

I_c, Collector Current (Amp)

0.3

0.5

1.0

3.0

Figure - 4 DC Current Gain

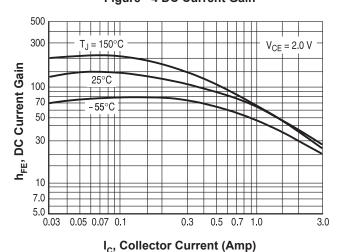
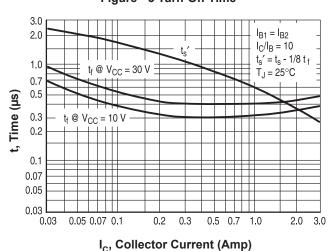


Figure - 5 Turn-Off Time

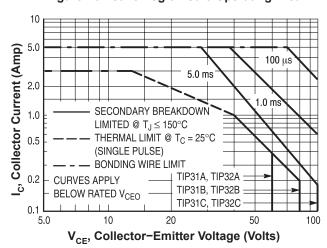




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Figure - 6 Active Region Safe Operating Area



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure - 6 curve is based on $T_{J(PK)} = 150^{\circ}C$; T_C is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 150^{\circ}C$, At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

Figure - 7 Collector Saturation Region

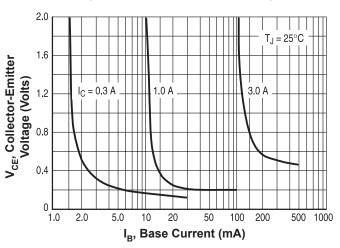


Figure - 8 Capacitances

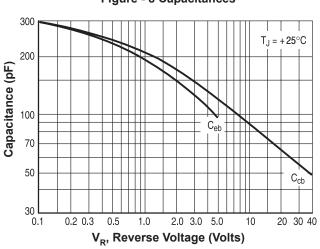


Figure - 9 "ON" Voltage

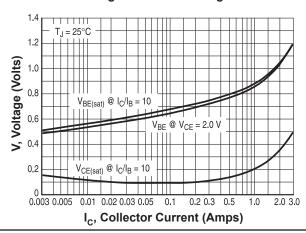
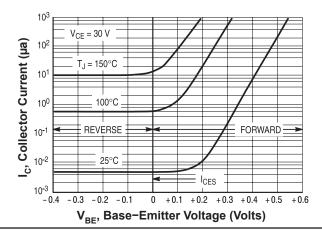


Figure - 10 Collector Cut-off Region



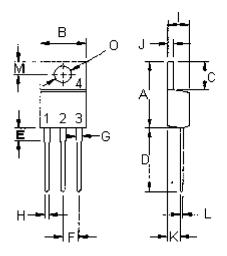
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Pin Configuration:

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector(Case)

Dimensions	Min.	Max.
Α	14.68	15.31
В	9.78	10.42
С	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
Н	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.2	2.97
L	0.33	0.55
M	2.48	2.98
0	3.7	3.9

Dimensions: Millimetres

Part Number Table

Description	Part Number		
Transistor NDN TO 220	TIP31A		
Transistor, NPN, TO-220	TIP31C		
Transistar DND TO 220	TIP32A		
Transistor, PNP, TO-220	TIP32C		

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